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#### Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

#### **Applications of Embedded - FPGAs**

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

#### Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	1584
Total RAM Bits	18432
Number of I/O	157
Number of Gates	60000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	201-VFBGA, CSBGA
Supplier Device Package	201-CSP (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/aglp060v2-csg201i

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IGLOO PLUS Device Family Overview

### SRAM and FIFO

IGLOO PLUS devices (except AGLP030 devices) have embedded SRAM blocks along their north side. Each variable-aspect-ratio SRAM block is 4,608 bits in size. Available memory configurations are 256×18, 512×9, 1k×4, 2k×2, and 4k×1 bits. The individual blocks have independent read and write ports that can be configured with different bit widths on each port. For example, data can be sent through a 4-bit port and read as a single bitstream. The embedded SRAM blocks can be initialized via the device JTAG port (ROM emulation mode) using the UJTAG macro (except in AGLP030 devices).

In addition, every SRAM block has an embedded FIFO control unit. The control unit allows the SRAM block to be configured as a synchronous FIFO without using additional core VersaTiles. The FIFO width and depth are programmable. The FIFO also features programmable Almost Empty (AEMPTY) and Almost Full (AFULL) flags in addition to the normal Empty and Full flags. The embedded FIFO control unit contains the counters necessary for generation of the read and write address pointers. The embedded SRAM/FIFO blocks can be cascaded to create larger configurations.

### PLL and CCC

IGLOO PLUS devices provide designers with very flexible clock conditioning circuit (CCC) capabilities. Each member of the IGLOO PLUS family contains six CCCs. One CCC (center west side) has a PLL. The AGLP030 device does not have a PLL or CCCs; it contains only inputs to six globals.

The six CCC blocks are located at the four corners and the centers of the east and west sides. One CCC (center west side) has a PLL.

The four corner CCCs and the east CCC allow simple clock delay operations as well as clock spine access.

The inputs of the six CCC blocks are accessible from the FPGA core or from one of several inputs located near the CCC that have dedicated connections to the CCC block.

The CCC block has these key features:

- Wide input frequency range (f<sub>IN CCC</sub>) = 1.5 MHz up to 250 MHz
- Output frequency range (f<sub>OUT CCC</sub>) = 0.75 MHz up to 250 MHz
- 2 programmable delay types for clock skew minimization
- Clock frequency synthesis (for PLL only)

Additional CCC specifications:

- Internal phase shift = 0°, 90°, 180°, and 270°. Output phase shift depends on the output divider configuration (for PLL only).
- Output duty cycle = 50% ± 1.5% or better (for PLL only)
- Low output jitter: worst case < 2.5% × clock period peak-to-peak period jitter when single global network used (for PLL only)
- Maximum acquisition time is 300 µs (for PLL only)
- Exceptional tolerance to input period jitter—allowable input jitter is up to 1.5 ns (for PLL only)
- + Four precise phases; maximum misalignment between adjacent phases (for PLL only) is 40 ps × 250 MHz /  $f_{OUT\ CCC}$

#### **Global Clocking**

IGLOO PLUS devices have extensive support for multiple clocking domains. In addition to the CCC and PLL support described above, there is a comprehensive global clock distribution network.

Each VersaTile input and output port has access to nine VersaNets: six chip (main) and three quadrant global networks. The VersaNets can be driven by the CCC or directly accessed from the core via multiplexers (MUXes). The VersaNets can be used to distribute low-skew clock signals or for rapid distribution of high-fanout nets.

#### I/Os with Advanced I/O Standards

The IGLOO PLUS family of FPGAs features a flexible I/O structure, supporting a range of voltages (1.2 V, 1.5 V, 1.8 V, 2.5 V, 3.0 V wide range, and 3.3 V). IGLOO PLUS FPGAs support many different I/O standards.

The I/Os are organized into four banks. All devices in IGLOO PLUS have four banks. The configuration of these banks determines the I/O standards supported.



## **Power Calculation Methodology**

This section describes a simplified method to estimate power consumption of an application. For more accurate and detailed power estimations, use the SmartPower tool in Libero SoC software.

The power calculation methodology described below uses the following variables:

- The number of PLLs as well as the number and the frequency of each output clock generated
- · The number of combinatorial and sequential cells used in the design
- · The internal clock frequencies
- · The number and the standard of I/O pins used in the design
- The number of RAM blocks used in the design
- Toggle rates of I/O pins as well as VersaTiles—guidelines are provided in Table 2-19 on page 2-14.
- Enable rates of output buffers—guidelines are provided for typical applications in Table 2-20 on page 2-14.
- Read rate and write rate to the memory—guidelines are provided for typical applications in Table 2-20 on page 2-14. The calculation should be repeated for each clock domain defined in the design.

#### Methodology

#### Total Power Consumption—PTOTAL

 $P_{TOTAL} = P_{STAT} + P_{DYN}$ 

P<sub>STAT</sub> is the total static power consumption.

P<sub>DYN</sub> is the total dynamic power consumption.

#### Total Static Power Consumption—PSTAT

P<sub>STAT</sub> = (PDC1 or PDC2 or PDC3) + N<sub>BANKS</sub> \* PDC5

 $N_{BANKS}$  is the number of I/O banks powered in the design.

### Total Dynamic Power Consumption—P<sub>DYN</sub>

P<sub>DYN</sub> = P<sub>CLOCK</sub> + P<sub>S-CELL</sub> + P<sub>C-CELL</sub> + P<sub>NET</sub> + P<sub>INPUTS</sub> + P<sub>OUTPUTS</sub> + P<sub>MEMORY</sub> + P<sub>PLL</sub>

#### Global Clock Contribution—P<sub>CLOCK</sub>

 $P_{CLOCK} = (PAC1 + N_{SPINE}*PAC2 + N_{ROW}*PAC3 + N_{S-CELL}*PAC4) * F_{CLK}$ 

N<sub>SPINE</sub> is the number of global spines used in the user design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *IGLOO PLUS FPGA Fabric User's Guide*.

N<sub>ROW</sub> is the number of VersaTile rows used in the design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *IGLOO PLUS FPGA Fabric User's Guide*.

F<sub>CLK</sub> is the global clock signal frequency.

N<sub>S-CELL</sub> is the number of VersaTiles used as sequential modules in the design.

PAC1, PAC2, PAC3, and PAC4 are device-dependent.

#### Sequential Cells Contribution—P<sub>S-CELL</sub>

 $P_{S-CELL} = N_{S-CELL} * (PAC5 + \alpha_1 / 2 * PAC6) * F_{CLK}$ 

 $N_{S\mbox{-}CELL}$  is the number of VersaTiles used as sequential modules in the design. When a multi-tile sequential cell is used, it should be accounted for as 1.

 $\alpha_{\text{1}}$  is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-19 on page 2-14.

F<sub>CLK</sub> is the global clock signal frequency.

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option <sup>1</sup>	Slew Rate	Capacitive Load (pF)	External Resistor ( $\Omega$ )	teouт	top	t <sub>DIN</sub>	tev)	tpys	teour	tzı	tzH	tız	t <sub>HZ</sub>	Units
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	12 mA	High	5 pF	-	0.98	2.31	0.19	0.99	1.37	0.67	2.34	1.86	2.65	3.38	ns
3.3 V LVCMOS Wide Range <sup>2</sup>	100 µA	12 mA	High	5 pF	Ι	0.98	3.21	0.19	1.32	1.92	0.67	3.21	2.52	3.73	4.73	ns
2.5 V LVCMOS	12 mA	12 mA	High	5 pF	-	0.98	2.29	0.19	1.19	1.40	0.67	2.32	1.94	2.65	3.27	ns
1.8 V LVCMOS	8 mA	8 mA	High	5 pF	-	0.98	2.45	0.19	1.12	1.61	0.67	2.48	2.16	2.71	3.16	ns
1.5 V LVCMOS	4 mA	4 mA	High	5 pF	-	0.98	2.71	0.19	1.26	1.80	0.67	2.75	2.39	2.78	3.15	ns
1.2 V LVCMOS	2 mA	2 mA	High	5 pF	-	0.98	3.38	0.19	1.57	2.34	0.67	3.26	2.78	2.99	3.24	ns
1.2 V LVCMOS Wide Range <sup>3</sup>	100 µA	2 mA	High	5 pF	-	0.98	3.38	0.19	1.57	2.34	0.67	3.26	2.78	2.99	3.24	ns

# Table 2-26 • Summary of I/O Timing Characteristics—Software Default Settings, STD Speed GradeCommercial-Case Conditions: TJ = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 3.0 V

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 μA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.

2. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.

All LVCMOS 1.2 V software macros support LVCMOS 1.2 V wide range as specified in the JESD8-12 specification.
 For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

## Single-Ended I/O Characteristics

### 3.3 V LVTTL / 3.3 V LVCMOS

Low-Voltage Transistor–Transistor Logic (LVTTL) is a general-purpose standard (EIA/JESD) for 3.3 V applications. It uses an LVTTL input buffer and push-pull output buffer.

3.3 V LVTTL / 3.3 V LVCMOS	v	IL	v	н	VOL	VOH	IOL	ЮН	IOSL	IOSH	IIL¹	IIH <sup>2</sup>
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA <sup>3</sup>	Max. mA <sup>3</sup>	μA <sup>4</sup>	μA <sup>4</sup>
2 mA	-0.3	0.8	2	3.6	0.4	2.4	2	2	25	27	10	10
4 mA	-0.3	0.8	2	3.6	0.4	2.4	4	4	25	27	10	10
6 mA	-0.3	0.8	2	3.6	0.4	2.4	6	6	51	54	10	10
8 mA	-0.3	0.8	2	3.6	0.4	2.4	8	8	51	54	10	10
12 mA	-0.3	0.8	2	3.6	0.4	2.4	12	12	103	109	10	10
16 mA	-0.3	0.8	2	3.6	0.4	2.4	16	16	103	109	10	10

#### Table 2-34 • Minimum and Maximum DC Input and Output Levels

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.

2. IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.

3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.

4. Currents are measured at 85°C junction temperature.

5. Software default selection highlighted in gray.

Test Point 
$$rac{1}{1}$$
  $rac{1}{1}$   $rac{1$ 

#### Figure 2-7 • AC Loading

#### Table 2-35 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C <sub>LOAD</sub> (pF)
0	3.3	1.4	5

*Note:* \**Measuring point = Vtrip. See Table 2-23 on page 2-20 for a complete table of trip points.* 

## static Microsemi.

IGLOO PLUS DC and Switching Characteristics

#### Timing Characteristics

#### Applies to 1.5 V DC Core Voltage

## Table 2-36 • 3.3 V LVTTL / 3.3 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage Commercial-Case Conditions: T<sub>1</sub> = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

			-									
Drive Strength	Speed Grade	t <sub>DOUT</sub>	t <sub>DP</sub>	t <sub>DIN</sub>	t <sub>PY</sub>	t <sub>PYS</sub>	t <sub>EOUT</sub>	t <sub>ZL</sub>	t <sub>zH</sub>	t <sub>LZ</sub>	t <sub>HZ</sub>	Units
2 mA	STD	0.97	3.94	0.18	0.85	1.15	0.66	4.02	3.46	1.82	1.87	ns
4 mA	STD	0.97	3.94	0.18	0.85	1.15	0.66	4.02	3.46	1.82	1.87	ns
6 mA	STD	0.97	3.20	0.18	0.85	1.15	0.66	3.27	2.94	2.04	2.27	ns
8 mA	STD	0.97	3.20	0.18	0.85	1.15	0.66	3.27	2.94	2.04	2.27	ns
12 mA	STD	0.97	2.72	0.18	0.85	1.15	0.66	2.78	2.57	2.20	2.53	ns
16 mA	STD	0.97	2.72	0.18	0.85	1.15	0.66	2.78	2.57	2.20	2.53	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

## Table 2-37 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage

#### Commercial-Case Conditions: T<sub>J</sub> = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Drive Strength	Speed Grade	t <sub>DOUT</sub>	t <sub>DP</sub>	t <sub>DIN</sub>	t <sub>PY</sub>	t <sub>PYS</sub>	t <sub>EOUT</sub>	t <sub>ZL</sub>	t <sub>zH</sub>	t <sub>LZ</sub>	t <sub>HZ</sub>	Units
2 mA	STD	0.97	2.36	0.18	0.85	1.15	0.66	2.41	1.90	1.82	1.98	ns
4 mA	STD	0.97	2.36	0.18	0.85	1.15	0.66	2.41	1.90	1.82	1.98	ns
6 mA	STD	0.97	1.96	0.18	0.85	1.15	0.66	2.01	1.56	2.04	2.38	ns
8 mA	STD	0.97	1.96	0.18	0.85	1.15	0.66	2.01	1.56	2.04	2.38	ns
12 mA	STD	0.97	1.76	0.18	0.85	1.15	0.66	1.80	1.39	2.20	2.64	ns
16 mA	STD	0.97	1.76	0.18	0.85	1.15	0.66	1.80	1.39	2.20	2.64	ns

Notes:

1. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

2. Software default selection highlighted in gray.

#### Applies to 1.2 V DC Core Voltage

# Table 2-38 • 3.3 V LVTTL / 3.3 V LVCMOS Low Slew – Applies to 1.2 V DC Core VoltageCommercial-Case Conditions: TJ = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 3.0 V

Drive Strength	Speed Grade	t <sub>DOUT</sub>	t <sub>DP</sub>	t <sub>DIN</sub>	t <sub>PY</sub>	t <sub>PYS</sub>	t <sub>EOUT</sub>	t <sub>ZL</sub>	t <sub>zH</sub>	t <sub>LZ</sub>	t <sub>HZ</sub>	Units
2 mA	STD	0.98	4.56	0.19	0.99	1.37	0.67	4.63	3.98	2.26	2.57	ns
4 mA	STD	0.98	4.56	0.19	0.99	1.37	0.67	4.63	3.98	2.26	2.57	ns
6 mA	STD	0.98	3.80	0.19	0.99	1.37	0.67	3.96	3.45	2.49	2.98	ns
8 mA	STD	0.98	3.80	0.19	0.99	137	0.67	3.86	3.45	2.49	2.98	ns
12 mA	STD	0.98	3.31	0.19	0.99	1.37	0.67	3.36	3.07	2.65	3.25	ns
16 mA	STD	0.98	3.31	0.19	0.99	1.37	0.67	3.36	3.07	2.65	3.25	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

#### Timing Characteristics

#### Applies to 1.5 V DC Core Voltage

## Table 2-60 • 1.5 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage

Commercial-Case Conditions: T<sub>J</sub> = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V

Drive Strength	Speed Grade	t <sub>DOUT</sub>	t <sub>DP</sub>	t <sub>DIN</sub>	t <sub>PY</sub>	t <sub>PYS</sub>	t <sub>EOUT</sub>	t <sub>ZL</sub>	t <sub>zH</sub>	t <sub>LZ</sub>	t <sub>HZ</sub>	Units
2 mA	STD	0.97	6.07	0.18	1.16	1.62	0.66	6.19	5.53	2.13	2.02	ns
4 mA	STD	0.97	5.24	0.18	1.16	1.62	0.66	5.34	4.81	2.37	2.47	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

# Table 2-61 • 1.5 V LVCMOS High Slew – Applies to 1.5 V DC Core VoltageCommercial-Case Conditions: TJ = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V

Drive Strength	Speed Grade	t <sub>DOUT</sub>	t <sub>DP</sub>	t <sub>DIN</sub>	t <sub>PY</sub>	t <sub>PYS</sub>	t <sub>EOUT</sub>	t <sub>ZL</sub>	t <sub>ZH</sub>	t <sub>LZ</sub>	t <sub>HZ</sub>	Units
2 mA	STD	0.97	2.65	0.18	1.16	1.62	0.66	2.71	2.43	2.13	2.11	ns
4 mA	STD	0.97	2.29	0.18	1.16	1.62	0.66	2.33	2.00	2.37	2.57	ns

Notes:

1. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

2. Software default selection highlighted in gray.

#### Applies to 1.2 V DC Core Voltage

#### Table 2-62 • 1.5 V LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage Commercial-Case Conditions: T<sub>J</sub> = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V

Drive Strength	Speed Grade	t <sub>DOUT</sub>	t <sub>DP</sub>	t <sub>DIN</sub>	t <sub>PY</sub>	t <sub>PYS</sub>	t <sub>EOUT</sub>	t <sub>ZL</sub>	t <sub>zH</sub>	t <sub>LZ</sub>	t <sub>HZ</sub>	Units
2 mA	STD	0.98	6.57	0.19	1.26	1.80	0.67	6.68	6.01	2.54	2.59	ns
4 mA	STD	0.98	5.72	0.19	1.26	1.80	0.67	5.81	5.27	2.79	3.05	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

#### Table 2-63 • 1.5 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage

#### Commercial-Case Conditions: T<sub>J</sub> = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V

Drive Strength	Speed Grade	t <sub>DOUT</sub>	t <sub>DP</sub>	t <sub>DIN</sub>	t <sub>PY</sub>	t <sub>PYS</sub>	t <sub>EOUT</sub>	t <sub>ZL</sub>	t <sub>ZH</sub>	t <sub>LZ</sub>	t <sub>HZ</sub>	Units
2 mA	STD	0.98	3.08	0.19	1.26	1.80	0.67	3.13	2.82	2.53	2.68	ns
4 mA	STD	0.98	2.71	0.19	1.26	1.80	0.67	2.75	2.39	2.78	3.15	ns

Notes:

1. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

2. Software default selection highlighted in gray.

## **Microsemi**.

IGLOO PLUS DC and Switching Characteristics

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t <sub>OCLKQ</sub>	Clock-to-Q of the Output Data Register	HH, DOUT
tosud	Data Setup Time for the Output Data Register	FF, HH
t <sub>OHD</sub>	Data Hold Time for the Output Data Register	FF, HH
t <sub>OCLR2Q</sub>	Asynchronous Clear-to-Q of the Output Data Register	LL, DOUT
t <sub>OREMCLR</sub>	Asynchronous Clear Removal Time for the Output Data Register	LL, HH
tORECCLR	Asynchronous Clear Recovery Time for the Output Data Register	LL, HH
t <sub>OECLKQ</sub>	Clock-to-Q of the Output Enable Register	HH, EOUT
t <sub>OESUD</sub>	Data Setup Time for the Output Enable Register	JJ, HH
t <sub>OEHD</sub>	Data Hold Time for the Output Enable Register	JJ, HH
t <sub>OECLR2Q</sub>	Asynchronous Clear-to-Q of the Output Enable Register	II, EOUT
t <sub>OEREMCLR</sub>	Asynchronous Clear Removal Time for the Output Enable Register	II, HH
t <sub>OERECCLR</sub>	Asynchronous Clear Recovery Time for the Output Enable Register	II, HH
t <sub>ICLKQ</sub>	Clock-to-Q of the Input Data Register	AA, EE
t <sub>ISUD</sub>	Data Setup Time for the Input Data Register	CC, AA
t <sub>IHD</sub>	Data Hold Time for the Input Data Register	CC, AA
t <sub>ICLR2Q</sub>	Asynchronous Clear-to-Q of the Input Data Register	DD, EE
t <sub>IREMCLR</sub>	Asynchronous Clear Removal Time for the Input Data Register	DD, AA
t <sub>IRECCLR</sub>	Asynchronous Clear Recovery Time for the Input Data Register	DD, AA

#### Table 2-73 • Parameter Definition and Measuring Nodes

Note: \*See Figure 2-13 on page 2-43 for more information.



## VersaTile Specifications as a Sequential Module

The IGLOO PLUS library offers a wide variety of sequential cells, including flip-flops and latches. Each has a data input and optional enable, clear, or preset. In this section, timing characteristics are presented for a representative sample from the library. For more details, refer to the *Fusion, IGLOO/e, and ProASIC3/E Macro Library Guide*.

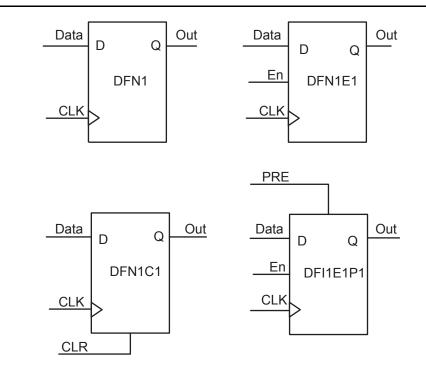


Figure 2-19 • Sample of Sequential Cells

## **Microsemi**.

IGLOO PLUS DC and Switching Characteristics

#### 1.2 V DC Core Voltage

#### Table 2-83 • Register Delays

#### Commercial-Case Conditions: T<sub>J</sub> = 70°C, Worst-Case VCC = 1.14 V

Parameter	Description	Std.	Units
t <sub>CLKQ</sub>	Clock-to-Q of the Core Register	1.61	ns
t <sub>SUD</sub>	Data Setup Time for the Core Register	1.17	ns
t <sub>HD</sub>	Data Hold Time for the Core Register	0.00	ns
t <sub>SUE</sub>	Enable Setup Time for the Core Register	1.29	ns
t <sub>HE</sub>	Enable Hold Time for the Core Register	0.00	ns
t <sub>CLR2Q</sub>	Asynchronous Clear-to-Q of the Core Register	0.87	ns
t <sub>PRE2Q</sub>	Asynchronous Preset-to-Q of the Core Register	0.89	ns
t <sub>REMCLR</sub>	Asynchronous Clear Removal Time for the Core Register	0.00	ns
t <sub>RECCLR</sub>	Asynchronous Clear Recovery Time for the Core Register	0.24	ns
t <sub>REMPRE</sub>	Asynchronous Preset Removal Time for the Core Register	0.00	ns
t <sub>RECPRE</sub>	Asynchronous Preset Recovery Time for the Core Register	0.24	ns
t <sub>WCLR</sub>	Asynchronous Clear Minimum Pulse Width for the Core Register	0.46	ns
t <sub>WPRE</sub>	Asynchronous Preset Minimum Pulse Width for the Core Register	0.46	ns
t <sub>CKMPWH</sub>	Clock Minimum Pulse Width High for the Core Register	0.95	ns
t <sub>CKMPWL</sub>	Clock Minimum Pulse Width Low for the Core Register	0.95	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.



#### Table 2-88 • AGLP060 Global Resource Commercial-Case Conditions: T<sub>J</sub> = 70°C, VCC = 1.14 V

		St	Std.	
Parameter	Description	Min. <sup>1</sup>	Max. <sup>2</sup>	Units
t <sub>RCKL</sub>	Input Low Delay for Global Clock	2.02	2.43	ns
t <sub>RCKH</sub>	Input High Delay for Global Clock	2.09	2.65	ns
t <sub>RCKMPWH</sub>	Minimum Pulse Width High for Global Clock	1.40		ns
t <sub>RCKMPWL</sub>	Minimum Pulse Width Low for Global Clock	1.65		ns
t <sub>RCKSW</sub>	Maximum Skew for Global Clock		0.56	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).

2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).

3. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.

### Table 2-89 • AGLP125 Global Resource

#### Commercial-Case Conditions: T<sub>J</sub> = 70°C, VCC = 1.14 V

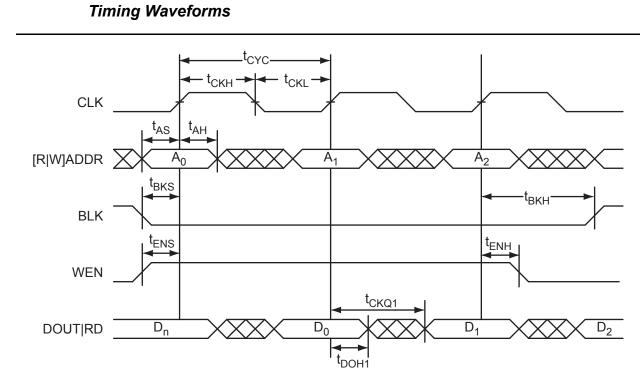
		Si	Std.		
Parameter	Description	Min. <sup>1</sup>	Max. <sup>2</sup>	Units	
t <sub>RCKL</sub>	Input Low Delay for Global Clock	2.08	2.54	ns	
t <sub>RCKH</sub>	Input High Delay for Global Clock	2.15	2.77	ns	
t <sub>RCKMPWH</sub>	Minimum Pulse Width High for Global Clock	1.40		ns	
t <sub>RCKMPWL</sub>	Minimum Pulse Width Low for Global Clock	1.65		ns	
t <sub>RCKSW</sub>	Maximum Skew for Global Clock		0.62	ns	

Notes:

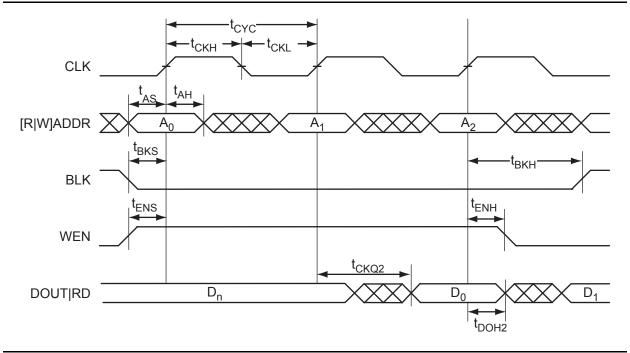
1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).

2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).

3. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.



#### Figure 2-24 • RAM Read for Pass-Through Output. Applicable to Both RAM4K9 and RAM512x18.



#### Figure 2-25 • RAM Read for Pipelined Output. Applicable to Both RAM4K9 and RAM512x18.

#### **Revision 17**



### *Timing Characteristics* 1.5 V DC Core Voltage

#### Table 2-92 • RAM4K9

#### Commercial-Case Conditions: T<sub>J</sub> = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	Std.	Units
t <sub>AS</sub>	Address setup time	0.69	ns
t <sub>AH</sub>	Address hold time	0.13	ns
t <sub>ENS</sub>	REN, WEN setup time 0		ns
t <sub>ENH</sub>	REN, WEN hold time	0.13	ns
t <sub>BKS</sub>	BLK setup time	1.37	ns
t <sub>BKH</sub>	BLK hold time	0.13	ns
t <sub>DS</sub>	Input data (DIN) setup time	0.59	ns
t <sub>DH</sub>	Input data (DIN) hold time	0.30	ns
t <sub>CKQ1</sub>	Clock High to new data valid on DOUT (output retained, WMODE = 0)	2.94	ns
	Clock High to new data valid on DOUT (flow-through, WMODE = 1)	2.55	ns
t <sub>CKQ2</sub>	Clock High to new data valid on DOUT (pipelined)		ns
t <sub>C2CWWL</sub> 1	Address collision clk-to-clk delay for reliable write after write on same address – applicable to closing edge		ns
t <sub>C2CRWH</sub> 1	Address collision clk-to-clk delay for reliable read access after write on same address – applicable to opening edge		ns
t <sub>C2CWRH</sub> 1	Address collision clk-to-clk delay for reliable write access after read on same address – applicable to opening edge		ns
t <sub>RSTBQ</sub>	RESET Low to data out Low on DOUT (flow-through)	1.72	ns
	RESET Low to data out Low on DOUT (pipelined)	1.72	ns
t <sub>REMRSTB</sub>	RESET removal	0.51	ns
t <sub>RECRSTB</sub>	RESET recovery	2.68	ns
t <sub>MPWRSTB</sub>	RESET minimum pulse width	0.68	ns
t <sub>CYC</sub>	Clock cycle time	6.24	ns
F <sub>MAX</sub>	Maximum frequency	160	MHz

Notes:

1. For more information, refer to the application note Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.

2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

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IGLOO PLUS DC and Switching Characteristics

### FIFO

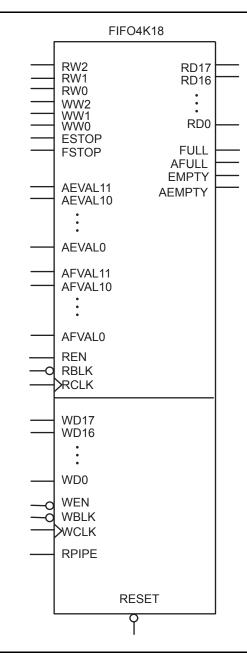


Figure 2-29 • FIFO Model

## **JTAG 1532 Characteristics**

JTAG timing delays do not include JTAG I/Os. To obtain complete JTAG timing, add I/O buffer delays to the corresponding standard selected; refer to the I/O timing characteristics in the "User I/O Characteristics" section on page 2-15 for more details.

#### **Timing Characteristics**

1.5 V DC Core Voltage

#### Table 2-100 • JTAG 1532

Commercial-Case Conditions: T<sub>J</sub> = 70°C, Worst-Case VCC = 1.425 V

Parameter	Parameter Description		Units
t <sub>DISU</sub>	Test Data Input Setup Time	1.00	ns
t <sub>DIHD</sub>	Test Data Input Hold Time	2.00	ns
t <sub>TMSSU</sub>	Test Mode Select Setup Time	1.00	ns
t <sub>TMDHD</sub>	Test Mode Select Hold Time	2.00	ns
t <sub>TCK2Q</sub>	Clock to Q (data out)	8.00	ns
t <sub>RSTB2Q</sub>	Reset to Q (data out)	25.00	ns
F <sub>TCKMAX</sub>	TCK Maximum Frequency	15	MHz
t <sub>TRSTREM</sub>	ResetB Removal Time	0.58	ns
t <sub>TRSTREC</sub>	ResetB Recovery Time	0.00	ns
t <sub>TRSTMPW</sub>	ResetB Minimum Pulse	TBD	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

#### 1.2 V DC Core Voltage

#### Table 2-101 • JTAG 1532

#### Commercial-Case Conditions: T<sub>J</sub> = 70°C, Worst-Case VCC = 1.14 V

Parameter	eter Description		Units
t <sub>DISU</sub>	Test Data Input Setup Time	1.50	ns
t <sub>DIHD</sub>	Test Data Input Hold Time	3.00	ns
t <sub>TMSSU</sub>	Test Mode Select Setup Time	1.50	ns
t <sub>TMDHD</sub>	Test Mode Select Hold Time	3.00	ns
t <sub>TCK2Q</sub>	Clock to Q (data out)	11.00	ns
t <sub>RSTB2Q</sub>	Reset to Q (data out)	30.00	ns
F <sub>TCKMAX</sub>	TCK Maximum Frequency	9.00	MHz
t <sub>TRSTREM</sub>	ResetB Removal Time	1.18	ns
t <sub>TRSTREC</sub>	ResetB Recovery Time	0.00	ns
t <sub>TRSTMPW</sub>	ResetB Minimum Pulse	TBD	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

#### Flash\*Freeze Mode Activation Pin

The FF pin is a dedicated input pin used to enter and exit Flash\*Freeze mode. The FF pin is active low, has the same characteristics as a single-ended I/O, and must meet the maximum rise and fall times. When Flash\*Freeze mode is not used in the design, the FF pin is available as a regular I/O.

When Flash\*Freeze mode is used, the FF pin must not be left floating to avoid accidentally entering Flash\*Freeze mode. While in Flash\*Freeze mode, the Flash\*Freeze pin should be constantly asserted.

The Flash\*Freeze pin can be used with any single-ended I/O standard supported by the I/O bank in which the pin is located, and input signal levels compatible with the I/O standard selected. The FF pin should be treated as a sensitive asynchronous signal. When defining pin placement and board layout, simultaneously switching outputs (SSOs) and their effects on sensitive asynchronous pins must be considered.

Unused FF or I/O pins are tristated with weak pull-up. This default configuration applies to both Flash\*Freeze mode and normal operation mode. No user intervention is required.

Table 3-1 shows the Flash\*Freeze pin location on the available packages for IGLOO and ProASIC3L devices. The Flash\*Freeze pin location is independent of device (except for a PQ208 package), allowing migration to larger or smaller IGLOO devices while maintaining the same pin location on the board. Refer to the "Flash\*Freeze Technology and Low Power Modes" chapter of the *IGLOO PLUS Device Family User's Guide* for more information on I/O states during Flash\*Freeze mode.

#### Table 3-1 • Flash\*Freeze Pin Location in IGLOO PLUS Devices

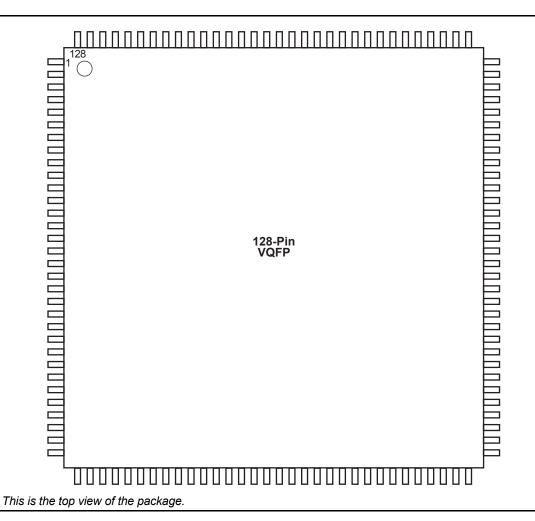
FF

Package	Flash*Freeze Pin	
CS281	W2	
CS201	R4	
CS289	U1	
VQ128	34	
VQ176	47	



# 4 – Package Pin Assignments

## VQ128



### Note

Note:

For Package Manufacturing and Environmental information, visit the Resource Center at http://www.microsemi.com/soc/products/solutions/package/docs.aspx.

Pin information is in the "Pin Descriptions" chapter of the IGLOO PLUS FPGA Fabric User's Guide.

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IGLOO PLUS Low Power Flash FPGAs

	CS281		CS281
Pin Number	AGLP125 Function	Pin Number	AGLP125 Function
R15	IO109RSB2	V10	IO133RSB2
R16	GDA1/IO103RSB1	V11	IO127RSB2
R18	GDB0/IO102RSB1	V12	IO123RSB2
R19	GDC0/IO100RSB1	V13	IO120RSB2
T1	IO171RSB3	V14	GND
T2	GEC0/IO169RSB3	V15	IO113RSB2
T4	GEB0/IO167RSB3	V16	GDA2/IO105RSB2
T5	IO157RSB2	V17	TDI
Т6	IO158RSB2	V18	VCCIB2
Τ7	IO148RSB2	V19	TDO
Т8	IO145RSB2	W1	GND
Т9	IO143RSB2	W2	FF/GEB2/IO163RSE 2
T10	GND	W3	IO155RSB2
T11	IO129RSB2	W4	IO152RSB2
T12	IO126RSB2	W5	IO150RSB2
T13	IO125RSB2	W6	IO147RSB2
T14	IO116RSB2	W7	IO142RSB2
T15	GDC2/IO107RSB2	W8	IO139RSB2
T16	TMS	W9	IO136RSB2
T18	VJTAG	W10	VCCIB2
T19	GDB1/IO101RSB1	W11	IO128RSB2
U1	IO160RSB2	W12	IO124RSB2
U2	GEA1/IO166RSB3	W13	IO119RSB2
U6	IO151RSB2	W14	IO115RSB2
U14	IO121RSB2	W15	IO114RSB2
U18	TRST	W16	IO110RSB2
U19	GDA0/IO104RSB1	W17	GDB2/IO106RSB2
V1	IO159RSB2	W18	ТСК
V2	VCCIB3	W19	GND
V3	GEC2/IO162RSB2		
V4	IO156RSB2		
V5	IO153RSB2		
V6	GND		
V7	IO144RSB2		
V8	IO141RSB2		

V9

IO140RSB2



Package Pin Assignments

	CS289		CS289	CS289	
Pin Number	AGLP060 Function	Pin Number	AGLP060 Function	Pin Number	AGLP060 Function
A1	GAB1/IO03RSB0	C5	VCCIB0	E9	IO22RSB0
A2	NC	C6	IO09RSB0	E10	IO26RSB0
A3	NC	C7	IO13RSB0	E11	VCCIB0
A4	GND	C8	IO15RSB0	E12	NC
A5	IO10RSB0	C9	IO21RSB0	E13	GBB1/IO33RSB0
A6	IO14RSB0	C10	GND	E14	GBA2/IO36RSB1
A7	IO16RSB0	C11	IO29RSB0	E15	GBB2/IO38RSB1
A8	IO18RSB0	C12	NC	E16	VCCIB1
A9	GND	C13	NC	E17	IO44RSB1
A10	IO23RSB0	C14	NC	F1	GFC1/IO140RSB3
A11	IO27RSB0	C15	GND	F2	IO142RSB3
A12	NC	C16	GBA0/IO34RSB0	F3	IO149RSB3
A13	NC	C17	IO39RSB1	F4	VCCIB3
A14	GND	D1	IO150RSB3	F5	GAB2/IO154RSB3
A15	NC	D2	IO151RSB3	F6	IO153RSB3
A16	NC	D3	GND	F7	NC
A17	GBC0/IO30RSB0	D4	GAB0/IO02RSB0	F8	IO08RSB0
B1	GAA1/IO01RSB0	D5	NC	F9	IO12RSB0
B2	GND	D6	NC	F10	NC
B3	NC	D7	NC	F11	NC
B4	NC	D8	GND	F12	NC
B5	IO07RSB0	D9	IO20RSB0	F13	GBC2/IO40RSB1
B6	NC	D10	IO25RSB0	F14	GND
B7	VCCIB0	D11	NC	F15	IO43RSB1
B8	IO17RSB0	D12	NC	F16	IO46RSB1
B9	IO19RSB0	D13	GND	F17	IO45RSB1
B10	IO24RSB0	D14	GBB0/IO32RSB0	G1	GFC0/IO139RSB3
B11	IO28RSB0	D15	GBA1/IO35RSB0	G2	GND
B12	VCCIB0	D16	IO37RSB1	G3	IO144RSB3
B13	NC	D17	IO42RSB1	G4	IO145RSB3
B14	NC	E1	VCCIB3	G5	IO146RSB3
B15	NC	E2	IO147RSB3	G6	IO148RSB3
B16	GBC1/IO31RSB0	E3	GAC2/IO152RSB3	G7	GND
B17	GND	E4	GAA2/IO156RSB3	G8	GND
C1	IO155RSB3	E5	GAC1/IO05RSB0	G9	VCC
C2	GAA0/IO00RSB0	E6	NC	G10	GND
C3	GAC0/IO04RSB0	E7	IO06RSB0	G11	GND
C4	NC	E8	IO11RSB0	G12	IO48RSB1

IGLOO PLUS Low Power Flash FPGAs

	CS289		CS289	CS289	
Pin Number	AGLP060 Function	Pin Number	AGLP060 Function	Pin Number	AGLP060 Function
G13	IO41RSB1	J17	GCA1/IO56RSB1	M4	IO122RSB3
G14	IO47RSB1	K1	GND	M5	GEB0/IO113RSB3
G15	IO49RSB1	K2	GFA0/IO135RSB3	M6	GEB1/IO114RSB3
G16	IO50RSB1	K3	GFB2/IO133RSB3	M7	NC
G17	GND	K4	IO128RSB3	M8	NC
H1	VCOMPLF	K5	IO123RSB3	M9	IO90RSB2
H2	GFB0/IO137RSB3	K6	IO125RSB3	M10	NC
H3	NC	K7	GND	M11	IO83RSB2
H4	IO141RSB3	K8	GND	M12	NC
H5	IO143RSB3	K9	GND	M13	GDA1/IO76RSB1
H6	GFB1/IO138RSB3	K10	GND	M14	GDA0/IO77RSB1
H7	GND	K11	GND	M15	IO71RSB1
H8	GND	K12	IO64RSB1	M16	IO69RSB1
H9	GND	K13	IO61RSB1	M17	VCCIB1
H10	GND	K14	IO66RSB1	N1	IO119RSB3
H11	GND	K15	IO65RSB1	N2	IO120RSB3
H12	GCC1/IO52RSB1	K16	GND	N3	GEC0/IO115RSB3
H13	IO51RSB1	K17	GCC2/IO60RSB1	N4	GEA0/IO111RSB3
H14	GCA0/IO57RSB1	L1	GFA2/IO134RSB3	N5	GND
H15	VCCIB1	L2	GFC2/IO132RSB3	N6	NC
H16	GCA2/IO58RSB1	L3	IO127RSB3	N7	IO104RSB2
H17	GCC0/IO53RSB1	L4	GND	N8	IO98RSB2
J1	VCCPLF	L5	IO121RSB3	N9	IO96RSB2
J2	GFA1/IO136RSB3	L6	GEC1/IO116RSB3	N10	VCCIB2
J3	VCCIB3	L7	GND	N11	NC
J4	IO131RSB3	L8	GND	N12	NC
J5	IO130RSB3	L9	VCC	N13	GDB2/IO79RSB2
J6	IO129RSB3	L10	GND	N14	NC
J7	VCC	L11	GND	N15	GND
J8	GND	L12	GDC1/IO72RSB1	N16	GDB0/IO75RSB1
J9	GND	L13	GDB1/IO74RSB1	N17	GDC0/IO73RSB1
J10	GND	L14	VCCIB1	P1	IO118RSB3
J11	VCC	L15	IO70RSB1	P2	IO117RSB3
J12	GCB2/IO59RSB1	L16	IO68RSB1	P3	GND
J13	GCB1/IO54RSB1	L17	IO67RSB1	P4	NC
J14	IO62RSB1	M1	IO126RSB3	P5	NC
J15	IO63RSB1	M2	VCCIB3	P6	IO106RSB2
J16	GCB0/IO55RSB1	M3	IO124RSB3	P7	IO99RSB2

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IGLOO PLUS Low Power Flash FPGAs

CS289		CS289	
Pin Number	AGLP125 Function	Pin Number	AGLP125 Function
P8	GND	T12	IO124RSB2
P9	IO132RSB2	T13	IO122RSB2
P10	IO125RSB2	T14	GND
P11	IO126RSB2	T15	IO115RSB2
P12	IO112RSB2	T16	TDI
P13	VCCIB2	T17	TDO
P14	IO108RSB2	U1	FF/GEB2/IO163RS
P15	GDA2/IO105RSB2		B2
P16	GDC2/IO107RSB2	U2	GND
P17	VJTAG	U3	IO151RSB2
R1	GND	U4	IO149RSB2
R2	GEA2/IO164RSB2	U5	IO146RSB2
R3	IO158RSB2	U6	IO142RSB2
R4	IO155RSB2	U7	GND
R5	IO150RSB2	U8	IO138RSB2
R6	VCCIB2	U9	IO136RSB2
R7	IO145RSB2	U10	IO133RSB2
R8	IO141RSB2	U11	IO129RSB2
R9	IO134RSB2	U12	GND
R10	IO130RSB2	U13	IO123RSB2
R11	GND	U14	IO120RSB2
R12	IO118RSB2	U15	IO117RSB2
R13	IO116RSB2	U16	ТСК
R14	IO114RSB2	U17	VPUMP
R15	IO110RSB2		
R16	TMS		
R17	TRST		
T1	GEA1/IO166RSB3		
T2	GEC2/IO162RSB2		
Т3	IO153RSB2		
T4	GND		
T5	IO147RSB2		
T6	IO143RSB2		
T7	IO140RSB2		
Т8	IO139RSB2		
Т9	VCCIB2		
T10	IO131RSB2		
110			